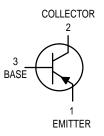
# **High Current Transistors PNP Silicon**



### **MAXIMUM RATINGS**

| Rating  | Symbol                            | BC<br>636   | BC<br>638          | BC<br>640     | Unit |
|---|-----------------------------------|-------------|--------------------|---------------|------|
| Collector-Emitter Voltage   | VCEO                              | -45         | <b>-45 -60 -80</b> |               | Vdc  |
| Collector-Base Voltage  | V <sub>СВО</sub>                  | -45         | -60                | -80           | Vdc  |
| Emitter-Base Voltage  | VEBO                              | -5.0        |                    |               | Vdc  |
| Collector Current — Continuous  | IC                                | -0.5        |                    | Adc           |      |
| Total Device Dissipation @ T <sub>A</sub> = 25°C<br>Derate above 25°C | PD                                | 625<br>5.0  |                    | mW<br>mW/°C   |      |
| Total Device Dissipation @ T <sub>C</sub> = 25°C<br>Derate above 25°C | PD                                | 1.5<br>12   |                    | Watt<br>mW/°C |      |
| Operating and Storage Junction<br>Temperature Range                   | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 |                    | °C            |      |

## THERMAL CHARACTERISTICS

| Characteristic                          | Symbol          | Max  | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 200  | °C/W |
| Thermal Resistance, Junction to Case    | $R_{\theta JC}$ | 83.3 | °C/W |

# $\textbf{ELECTRICAL CHARACTERISTICS} \ (T_{A} = 25^{\circ}\text{C unless otherwise noted})$

| Characteristic  |                         | Symbol   | Min               | Тур         | Max         | Unit         |
|---|-------------------------|----------|-------------------|-------------|-------------|--------------|
| OFF CHARACTERISTICS   |                         |          |                   |             |             |              |
| Collector-Emitter Breakdown Voltage* (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)  | BC636<br>BC638<br>BC640 | V(BR)CEO | -45<br>-60<br>-80 | _<br>_<br>_ | _<br>_<br>_ | Vdc          |
| Collector-Base Breakdown Voltage (I <sub>C</sub> = -100 μAdc, I <sub>E</sub> = 0)   | BC636<br>BC638<br>BC640 | V(BR)CBO | -45<br>-60<br>-80 | _<br>_<br>_ | _<br>_<br>_ | Vdc          |
| Emitter-Base Breakdown Voltage (I <sub>E</sub> = -10 μAdc, I <sub>C</sub> = 0)  |                         | V(BR)EBO | -5.0              | _           | _           | Vdc          |
| Collector Cutoff Current<br>$(V_{CB} = -30 \text{ Vdc}, I_{E} = 0)$<br>$(V_{CB} = -30 \text{ Vdc}, I_{E} = 0, T_{A} = 125^{\circ}\text{C})$ |                         | ICBO     | _<br>_<br>_       | _<br>_      | -100<br>-10 | nAdc<br>μAdc |

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle 2.0%.

BC636 BC638 BC640



### **BC636 BC638 BC640**

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

| Characteristic   | Symbol          | Min                              | Тур           | Max      | Unit |  |
|--|-----------------|----------------------------------|---------------|----------|------|--|
| ON CHARACTERISTICS <sup>(1)</sup>  |                 |                                  |               |          |      |  |
| DC Current Gain  | hFE             | 25<br>40<br>40<br>40<br>40<br>25 |               |          |      |  |
| Collector-Emitter Saturation Voltage (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)               | VCE(sat)        | _<br>_                           | -0.25<br>-0.5 | -0.5<br> | Vdc  |  |
| Base–Emitter On Voltage<br>(I <sub>C</sub> = -500 mAdc, V <sub>CE</sub> = -2.0 Vdc)                        | VBE(on)         | _                                | _             | -1.0     | Vdc  |  |
| DYNAMIC CHARACTERISTICS  |                 |                                  |               |          |      |  |
| Current – Gain — Bandwidth Product<br>(I <sub>C</sub> = –50 mAdc, V <sub>CE</sub> = –2.0 Vdc, f = 100 MHz) | fT              | _                                | 150           | _        | MHz  |  |
| Output Capacitance<br>(V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)                         | C <sub>ob</sub> | _                                | 9.0           | _        | pF   |  |
| Input Capacitance<br>(VEB = -0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)                                     | C <sub>ib</sub> | _                                | 110           | _        | pF   |  |

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300~\mu s,$  Duty Cycle 2.0%.

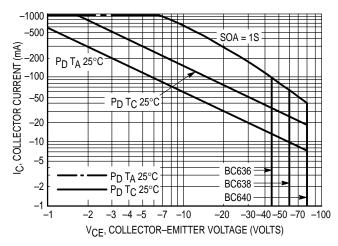


Figure 1. Active Region Safe Operating Area

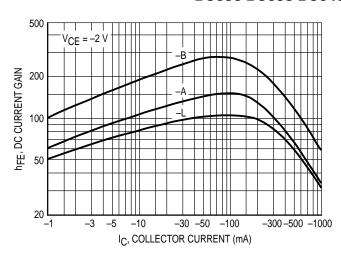


Figure 2. DC Current Gain

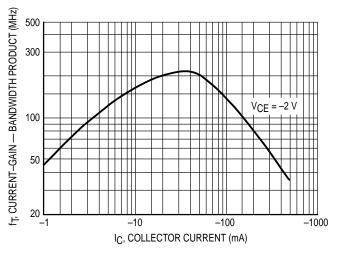


Figure 3. Current Gain Bandwidth Product

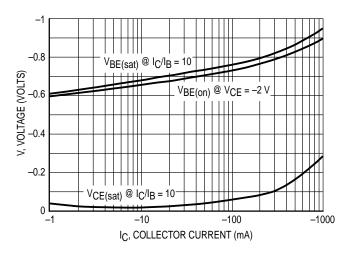
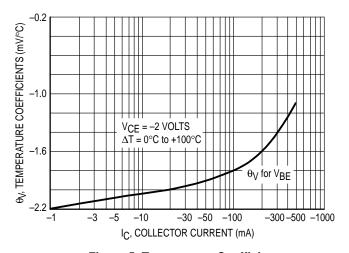
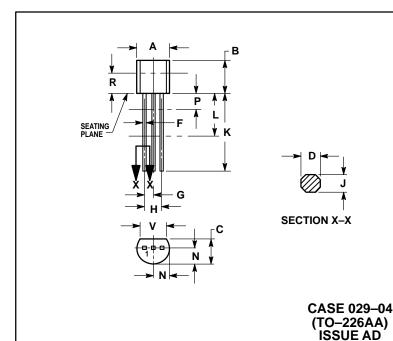


Figure 4. "Saturation" and "On" Voltages



**Figure 5. Temperature Coefficients** 

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
  DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

|     | INC   | HES   | MILLIN | IETERS |
|-----|-------|-------|--------|--------|
| DIM | MIN   | MAX   | MIN    | MAX    |
| Α   | 0.175 | 0.205 | 4.45   | 5.20   |
| В   | 0.170 | 0.210 | 4.32   | 5.33   |
| С   | 0.125 | 0.165 | 3.18   | 4.19   |
| D   | 0.016 | 0.022 | 0.41   | 0.55   |
| F   | 0.016 | 0.019 | 0.41   | 0.48   |
| G   | 0.045 | 0.055 | 1.15   | 1.39   |
| Н   | 0.095 | 0.105 | 2.42   | 2.66   |
| J   | 0.015 | 0.020 | 0.39   | 0.50   |
| K   | 0.500 |       | 12.70  |        |
| L   | 0.250 |       | 6.35   |        |
| N   | 0.080 | 0.105 | 2.04   | 2.66   |
| Р   |       | 0.100 |        | 2.54   |
| R   | 0.115 |       | 2.93   |        |
| ٧   | 0.135 |       | 3.43   |        |

STYLE 14:

PIN 1. EMITTER

2. COLLECTOR BASE

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